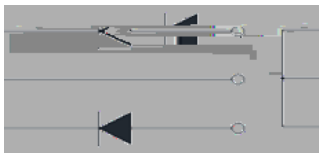
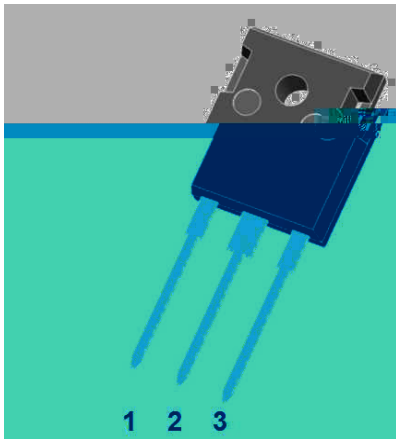




Schottky Diodes



Features

- ✓ High frequency operation
- ✓ Low forward voltage drop
- ✓ High purity , high temperature epoxy encapsulation for enhanced mechanical strength
- ✓ 7 H U P L T D plated leads , solderable
- 002 and JESD22-B102
- ✓ Polarity: As marked

Maximum Ratings ($T_a = 25^\circ\text{C}$ Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	MBR20200PT
Device marking code			MBR20200PT
Repetitive Peak Reverse Voltage	V _{RRM}	V	200
Average Rectified Output Current @60 Hz sine wave , R-load = 15%	I _O	A	20
Surge(Non-repetitive)Forward Current @60 Hz half sine-wave , 1 cycle , $T_a = 25^\circ\text{C}$	I _{FSM}	A	200
Current Squared Time @1ms to 8.3ms $T_j = 25^\circ\text{C}$	I ² t	A ² s	166
Storage Temperature	T _{stg}	°C	-55 ~ +175
Junction Temperature	T _j	°C	-55 ~ +175

Electrical Characteristics

PARAMETER	SYMBOL	UNIT	TEST CONDITIONS	Min	Typ	Max
Peak Forward Current $T_j = 25^\circ\text{C}$	I _F	A	Peak Forw = 10.0A $T_j = 25^\circ\text{C}$	0.68	0.72	
DC reverse current at rated DC blocking voltage per diode	I _{RRM1}	mA		-	-	20
Junction capacitance	C _j	pF	1MHz Applied Voltage and Reverse of 4.0 V.D.C.	100	158	300

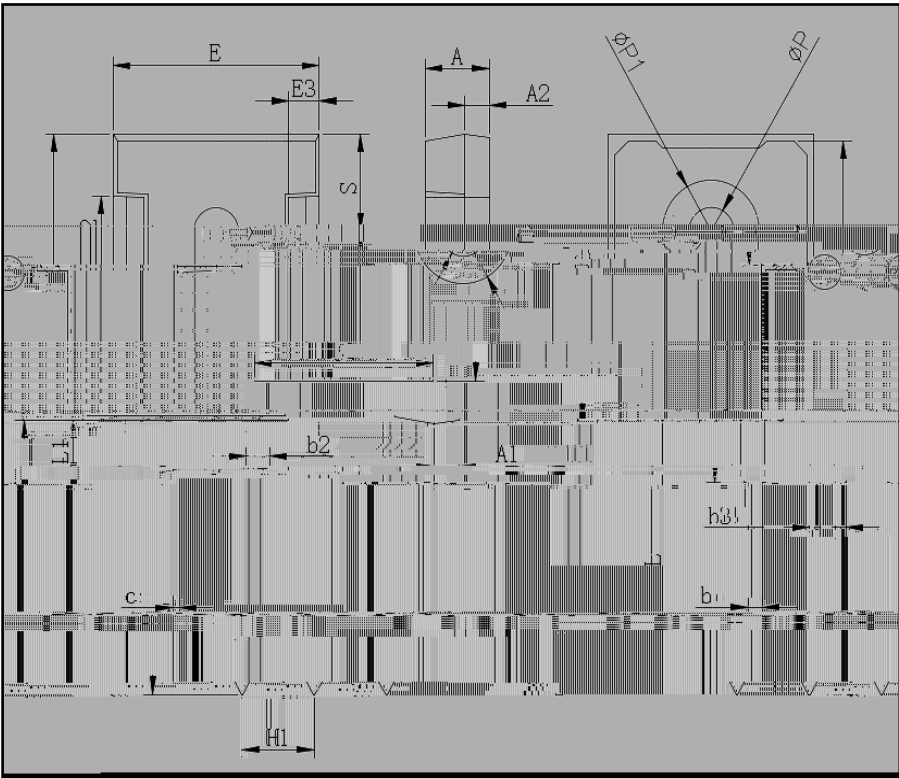
Note1:Pulse test:300uS pulse width , 1% duty cycle

Note2:Pulse test:pulse width 40mS



MBR20200PT

Outline Dimensions



TO-247AB		
Dim	Min	Max
A	4.80	5.20
A1	2.21	2.61
A2	1.85	2.15
b	1.0	1.4
b2	1.91	2.21
C	0.5	0.7
D	20.70	21.30
D1	16.25	16.85
E	15.50	16.10
E1	13.0	13.6
E2	4.80	5.20
E3	2.30	2.70
L	19.62	20.22
L1	-	4.30
Ů P	3.40	3.80
Ů P1	-	7.30
S	6.15 TYP	
H1	5.44TYP	
b3	2.80	3.20

